



Contemporary pseudopotentials—Simple reliability criteria

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discussions of common misconceptions regarding pseudopotentials is

PACS numbers: 71.10. + x, 73.20. - r, 31.70. - f

I. INTRODUCTION

questions have been raised pertaining
to the octet rule concerning
the structure of molecules.

The electron density ψ_e is a sum of atomic orbital (AO) contributions $\psi_{e,i}$, where i denotes the AO index. The AO $\psi_{e,i}$ is referred to as a screening or valence orbital. The AO $\psi_{e,i}$ is composed of a core part $\psi_{e,i}^c$ and a valence part $\psi_{e,i}^v$. The core part $\psi_{e,i}^c$ is the orbital that is localized around the nucleus of the atom i . The valence part $\psi_{e,i}^v$ is the orbital that is delocalized over the entire molecule. The total electron density ψ_e is the sum of all atomic orbital contributions $\psi_{e,i}$.

UDOPOTENTIALS

pseudopotential. It is often presented as a sum over all atoms:

e approaches underlying a treatment as ICPG, or in the system (with position-ve

perturbative approaches). We first establish the necessary

where $\hat{P}_{l,i}$ is the l th angular momentum projector with respect to the i th center.

An atomic pseudopotential that can be expressed as angular momentum dependent (and hence acts differently on different angular momentum components of the wavefunction)

$$-\frac{1}{2}\nabla^2 + V_{c,v}[\rho(\mathbf{r},\mathbf{r}')]\psi_j^{c,v}(\mathbf{r}') = \epsilon_j \psi_j^{c,v}(\mathbf{r}), \quad (1)$$

Lectron in the pseud

The pseudopotential approach attempts to replace an electron (i.e., core and valence wavefunctions treated on the same footing) eigenvalue problem:

...and he did it.

is referred to as the "affection potential." In the present paper we will introduce a new method for calculating affection potential.

$$\{x_i(\Gamma)\}_{i=1}^n \in X_j(\Gamma) = \{x_j(\Gamma)\}_{j=1}^n$$

Figure 1. $\Delta\tau(l_1, l_2, \dots, l_N) = \tau(l_1) \tau(l_2) \dots \tau(l_{N-1}) \tau(l_N)$ includes electron-nucleus interactions, interatomic interactions, and

which applies to the valence

require that the normalized pseudo-orbitals χ_{nl} span the space characteristics of the all-electron density function.

is-nator carri and jones² (or Si) in which the orbital energies as well as the wavefunctions of a density-functional Si

atom were fitted within a postulated core form $V_{core}(r)$. A good fit has been achieved within a "hard-core" (strongly repulsive

(9) at small- r) form. A similar approach has been successfully applied by Louie to a Pd surface.¹⁶ As this approach is com-

pletely non-empirical, the error in correlation effects can be assessed. Recent tests on the Si₂ molecule² and bulk Si⁴ indicate

such a unitary mixing. In addition, one can

of the calculation the true valence orbitals.

orthogonalization

unconventional basis functions (e.g., $ps(r)$) have given microscopic electronic structure theory

an ansatz as there

ca rule that dictates shape at small r . No

valence orbitals are used. The form of

to fit some *theoretical* constructs of an all-electron calculation on a reference system. A recent example of a model potential problem:

$$\sum_n \frac{Q^{(1)}_{nl}}{n} \psi_{nl}^* \psi_{nl}$$

$$n(\mathbf{r}) = \sum_{nl} X_{nl}(\mathbf{r}) \chi_{nl}$$

where the sum extends on all (known) core and valence

details of symmetry

F. First principles pseudopotentials

recover at the

simply by core

electronic configuration (g) of the atom and solves Eqs. (8)

is no simple

and (9) for the potential $V_{pseud}(r)$ that uses (these Lagrange

empirical data

3. Difficulties with the DF and TDF pseudopotentials

forms a good first order approximation to the crystalline density and neariv localized states in molecules and surfaces carry many of the characteristics of the atoms to the extent that the atomic and ionic pseudo-wavefunctions mimic closely those of the valence orbitals outside the core region. In a wide range of ground and excited states (i.e. configurations

TABLE II. Comparison of the Si orbital energies (ϵ_{3s} , ϵ_{3p} , and ϵ_{3d}) and total energy differences (ΔE_t) for the $3s^23p^2$ configuration of the silicon atom. The reference values are taken from the Hartree-Fock calculations of the $3s^23p^2$ configuration by TDF. The nonlocal density functionals (NDF) are the model local potentials of Harris and Jones; SEMP is the local-semiempirical Berkeley potential. The ΔE_t values are the total energy differences between the Hartree-Fock reference and the various functionals. The ΔE_t values are given in parentheses.

	ϵ_{3s}	ϵ_{3p}	ϵ_{3d}	ΔE_t	
$3s^23p^2$					
AE	−2.006	−9.779 [−0.01]	−3.209 [−0.03]	...	
TDF	...	−9.782 [−0.01]	−3.209 [−0.03]	0.0	
SX	...	−9.783 [−0.01]	−3.209 [−0.03]	0.0	
MODEL	...	−9.585 [−0.19]	−3.238 [−0.03]	0.0	
SEMP	...	−10.000 [−0.62]	−3.289 [−0.08]	−0.0	
$3s13p^3$					
AE	−10.522	−3.764	...	6.664	
TDF	−10.525 [0.003]	−3.766 [0.002]	...	6.669 [−0.005]	
MODEL	...	−10.480 [−0.04]	−3.738 [−0.03]	...	
SEMP	...	−10.305 [−0.22]	−3.782 [0.02]	...	
SFMP	...	−11.307 [0.79]	−3.912 [0.15]	...	
$3s13p^23d^0.5$					
AE	−6.255	−0.199 [−0.01]	−0.184 [−0.01]	AE	
TDF	−6.255 [0.00]	−0.199 [0.00]	9.188 [−0.004]	TDF	
DF	−6.255 [0.00]	−0.199 [0.00]	9.158 [0.03]	DF	
MODEL	
SEMP	
SFMP	
$3s13p^23d^1$					
AE	−3.249	14.038	AE	−18.571	
TDF	−3.250 [0.001]	14.041 [−0.003]	TDF	−18.562 [−0.01]	
DF	−3.251 [0.002]	14.027 [−0.01]	DF	−18.648 [−0.06]	
MODEL	
SEMP	
SFMP	
$3s13p^23d^2$					
AE	−27.932 [−0.06]	−20.032 [−0.05]	−10.320 [0.02]	29.589 [0.02]	AE
TDF	−28.307 [−0.31]	−20.357 [−0.11]	TDF
DF	−28.389 [−0.05]	...
MODEL
SEMP
SFMP

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electron moments. Numbers in brackets indicate percent error relative to

TABLE II. Comparison of the s and p pseudofrictional moments with the

	$\langle \hat{p}^2 \rangle_{\text{SEMP}} (\text{au})$	$\langle \hat{p}^2 \rangle_{\text{AE}} (\text{au})$	$\langle \hat{p}^2 \rangle_{\text{TDF}} (\text{au})$	$\langle \hat{p}^2 \rangle_{\text{DF}} (\text{au})$	$\langle \hat{p}^2 \rangle_{\text{MODEL}} (\text{au})$	$\langle \hat{p}^2 \rangle_{\text{SRMP}} (\text{au})$
$3s^23p^2$						
10.083	AE	2.178		2.877		5.555
10.081 [0.02%]	TDF	2.180 [-0.1%]		2.887 [-0.35%]		5.553 [0.04%]
5.337 [3.9%]		9.839 [2.4%]			20.10 [3.1%]	2.840 [1.1%]
-6.03 [-8.6%]		10.265 [-5.7%]			23.00 [-5.6%]	2.993 [-1.1%]
2.144	SEMP	2.311 [-6.1%]		3.009 [-4.6%]		6.738 [+3.3%]
2.157 [0.6%]		2.780 [-0.4%]			9.278 [-0.1%]	
2.073 [3.3%]		2.717 [1.8%]		5.137 [4.3%]		8.968 [3.2%]
2.270 [+5.9%]		2.894 [-4.6%]		5.858 [+9.1%]		9.887 [+6.7%]
2.320 [-4.0%]		2.893 [-4.0%]				

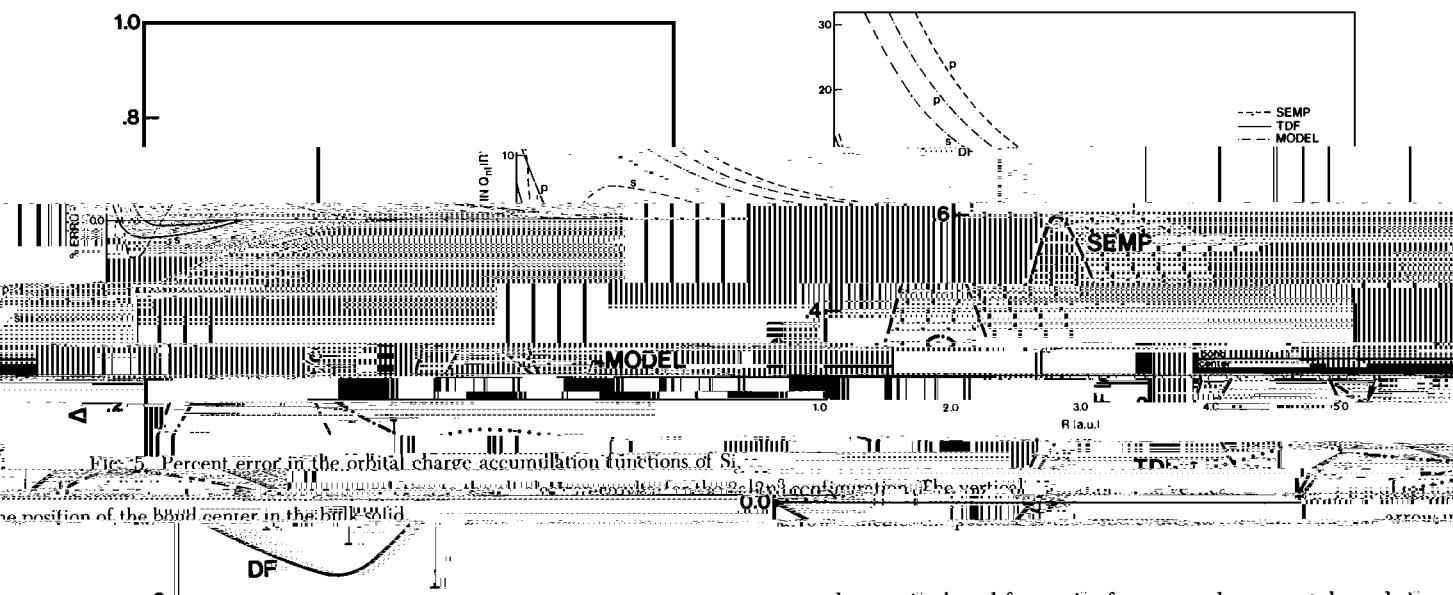


Fig. 5. Percent error in the orbital charge accumulation functions of Si.

Figure 10. The effect of the vertical configuration on the energy difference between the DF and DF₀ configurations. The vertical configuration is defined as the ratio of the vertical distance between the two centers of the DF molecule to the horizontal distance between them.

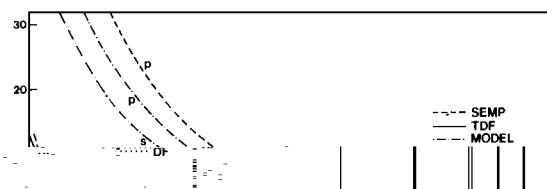
It is seen that the SEMP and MODEL pseudopotentials produce values for L_{eff} that are considerably too large (in

errors are important, while the most important errors are smaller than 1%.

te that in general it is not sufficient to ensure the correctness of the electron results! The vertical bars indicate the mag-

In the core-potential approach, the core-attraction is treated as a fixed potential, and the core-potential approach, the core-attraction is also modified relative to the all-electron case. This leads to the possibility

be partially offset by the errors in the Coulomb repulsion introduced by the accumulation of excess charge in the bond.



SEMPE

Fig. 3. The errors in the pseudopotential x-ray scattering factor relative to the value of the pseudopotential Coulomb (and exchange) interaction at the first few reciprocal lattice vectors also modified leads to the possibility

that the errors in the attraction terms of potentials, introduced by the penetration of charge into the core (and reflected by overly attractive forces) are negligible and simulations made with such potentials are reliable.

the soft semiempirical local Si pseudopotentials (see also Ref. 1) are described by the valence core functions.

constitutes an enormous simplification over the direct solution of the all-electron problem, such a core orthogonalization (performed *after* the completion of the solution of the nseu-

TABLE IV. First principals density-functional results for the band gaps of some cubic materials compared with experimental data.

¹³M. Lüscher, *Fortschritte der Physik*, **18**, M. Lüscher, M. Gell-Mann, J. B. Gammel, *ibid.*, **19**, 141 (1970).
¹⁴J. A. Appelbaum and D.R. Hammann, *Phys. Rev. B*, **8**, 1777 (1973).